



Publisher Correction to: Effect of strain modification on crystallinity and luminescence of InGaN/GaN multiple quantum wells grown by MOCVD

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The corresponding author of this article is Prof. Zhiyong Wang, E-Mail: zywang_bjut@126.com.
Please excuse this mistake.
The original article was corrected.

Dear readers,

Unfortunately, the original version of this article did not correctly reflect the change of authorship.

The original article can be found online at <https://doi.org/10.1007/s00339-018-1958-x>.

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